

MOS FIELD EFFECT TRANSISTOR NP70N10KUF

SWITCHING N-CHANNEL POWER MOS FET

DESCRIPTION

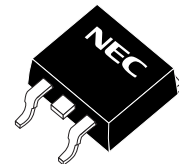
The NP70N10KUF is N-channel MOS Field Effect Transistor designed for high current switching applications.

ORDERING INFORMATION

PART NUMBER	LEAD PLATING	PACKING	PACKAGE
NP70N10KUF-E1-AZ ^{Note}	Pure Sn (Tin)	Tape	TO-263 (MP-25ZK)
NP70N10KUF-E2-AZ ^{Note}		800 p/reel	typ. 1.5 g

Note See "TAPE INFORMATION"

(TO-263)



FEATURES

- Channel temperature 175 degree rating
- Super low on-state resistance
 $R_{DS(on)} = 20 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 35 \text{ A)}$
- Low C_{iss} : $C_{iss} = 2500 \text{ pF TYP.}$

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Drain to Source Voltage ($V_{GS} = 0 \text{ V}$)	V_{DSS}	100	V
Gate to Source Voltage ($V_{DS} = 0 \text{ V}$)	V_{GSS}	± 20	V
Drain Current (DC) ($T_C = 25^\circ\text{C}$)	$I_{D(DC)}$	± 70	A
Drain Current (pulse) ^{Note1}	$I_{D(pulse)}$	± 135	A
Total Power Dissipation ($T_A = 25^\circ\text{C}$)	P_{T1}	1.8	W
Total Power Dissipation ($T_C = 25^\circ\text{C}$)	P_{T2}	120	W
Channel Temperature	T_{ch}	175	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +175	$^\circ\text{C}$
Single Avalanche Current ^{Note2}	I_{AS}	22	A
Single Avalanche Energy ^{Note2}	E_{AS}	48	mJ

Notes 1. $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$

2. Starting $T_{ch} = 25^\circ\text{C}$, $V_{DD} = 50 \text{ V}$, $R_G = 25 \Omega$, $V_{GS} = 20 \rightarrow 0 \text{ V}$, $L = 100 \mu\text{H}$

THERMAL RESISTANCE

Channel to Case Thermal Resistance	$R_{th(ch-C)}$	1.25	$^\circ\text{C/W}$
Channel to Ambient Thermal Resistance	$R_{th(ch-A)}$	83.3	$^\circ\text{C/W}$

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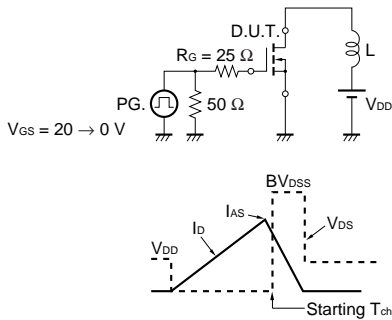
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ELECTRICAL CHARACTERISTICS (T_A = 25°C)

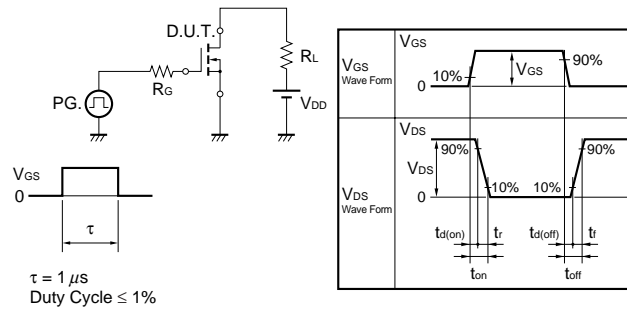
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain to Source Breakdown Voltage	BV _{DSS}	I _D = 250 μA, V _{GS} = 0 V	100			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V			10	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±20 V, V _{DS} = 0 V			±100	nA
Gate to Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.7	2.5	3.3	V
Forward Transfer Admittance ^{Note}	y _{fs}	V _{DS} = 10 V, I _D = 20 A	11	22		S
Drain to Source On-state Resistance ^{Note}	R _{DS(on)}	V _{GS} = 10 V, I _D = 35 A		17	20	mΩ
Input Capacitance	C _{iss}	V _{DS} = 25 V		2500	3750	pF
Output Capacitance	C _{oss}	V _{GS} = 0 V		270	410	pF
Reverse Transfer Capacitance	C _{rss}	f = 1 MHz		110	200	pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 50 V, I _D = 35 A		25	53	ns
Rise Time	t _r	V _{GS} = 10 V		9	23	ns
Turn-off Delay Time	t _{d(off)}	R _G = 0 Ω		48	96	ns
Fall Time	t _f			7	18	ns
Total Gate Charge	Q _G	V _{DD} = 80 V		50	75	nC
Gate to Source Charge	Q _{GS}	V _{GS} = 10 V		16		nC
Gate to Drain Charge	Q _{GD}	I _D = 70 A		19		nC
Body Diode Forward Voltage ^{Note}	V _{F(S-D)}	I _F = 70 A, V _{GS} = 0 V		1.0	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 70 A, V _{GS} = 0 V		88		ns
Reverse Recovery Charge	Q _{rr}	di/dt = 100 A/μs		245		nC

Note Pulsed

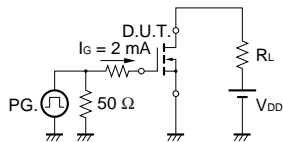
TEST CIRCUIT 1 AVALANCHE CAPABILITY



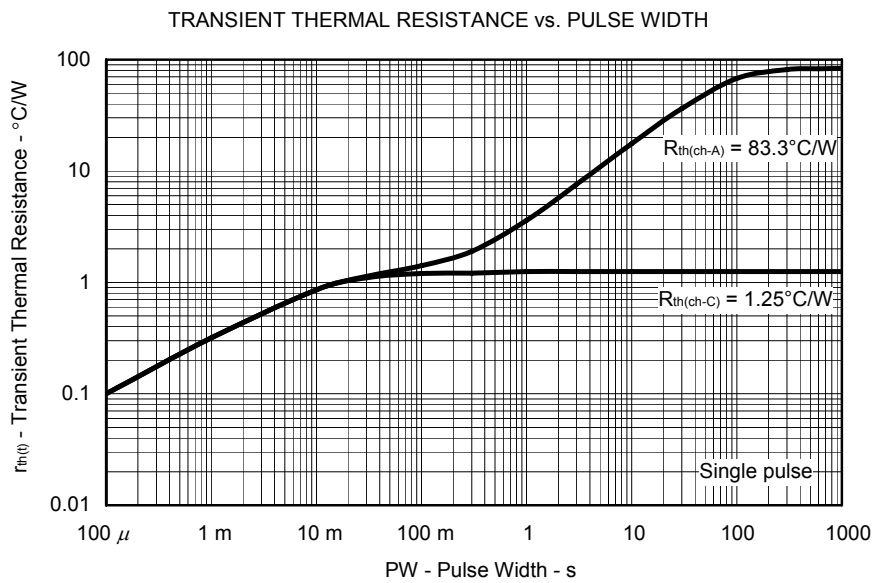
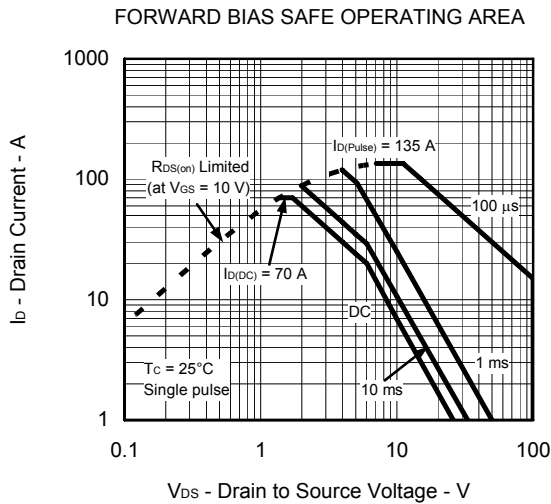
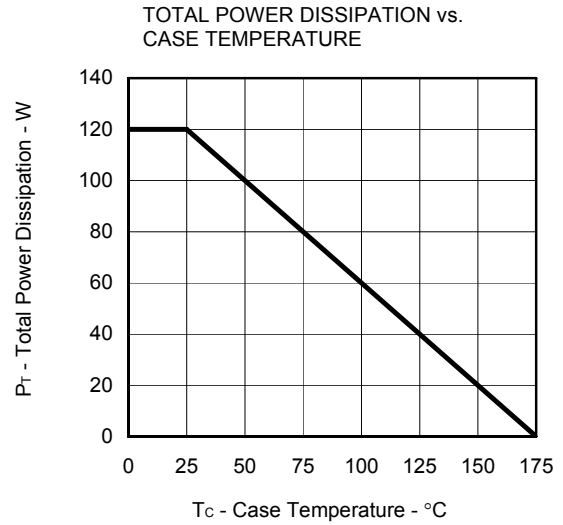
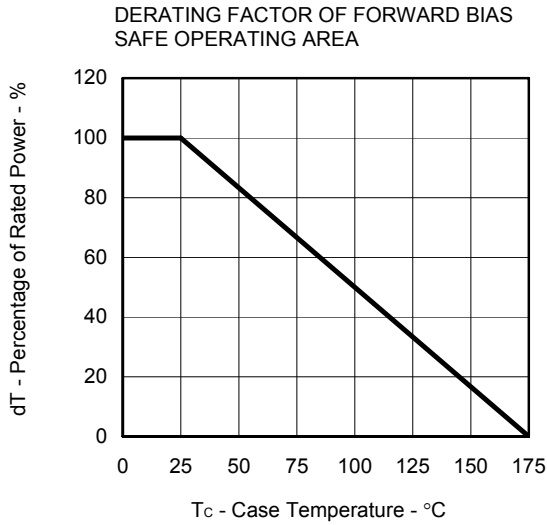
TEST CIRCUIT 2 SWITCHING TIME



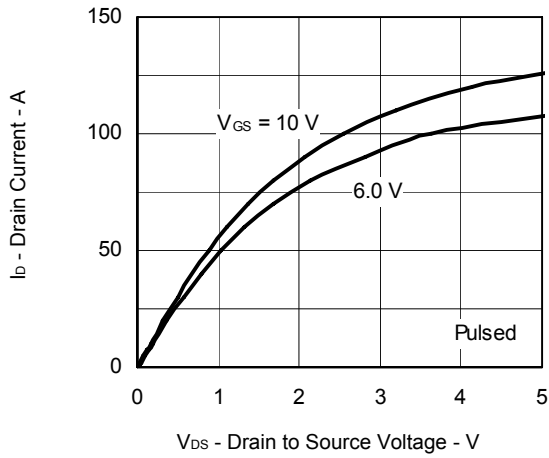
TEST CIRCUIT 3 GATE CHARGE



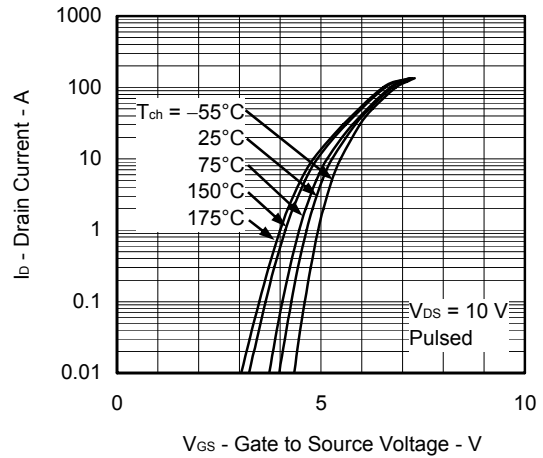
TYPICAL CHARACTERISTICS (T_A = 25°C)



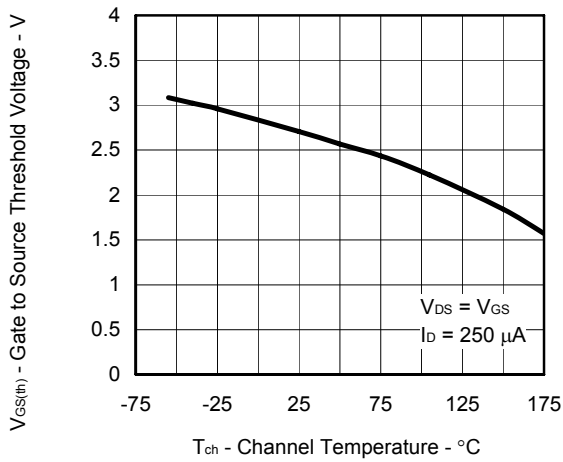
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



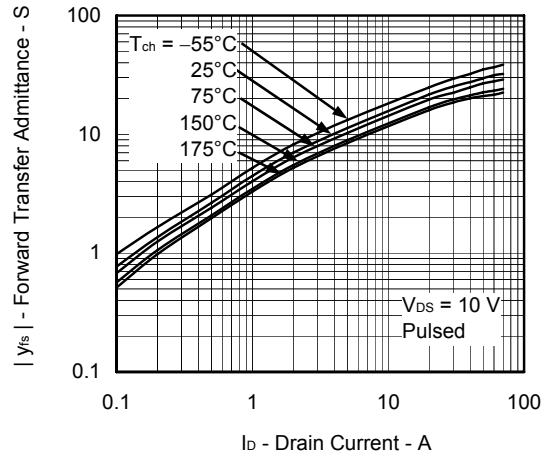
DRAIN CURRENT vs. GATE TO SOURCE VOLTAGE



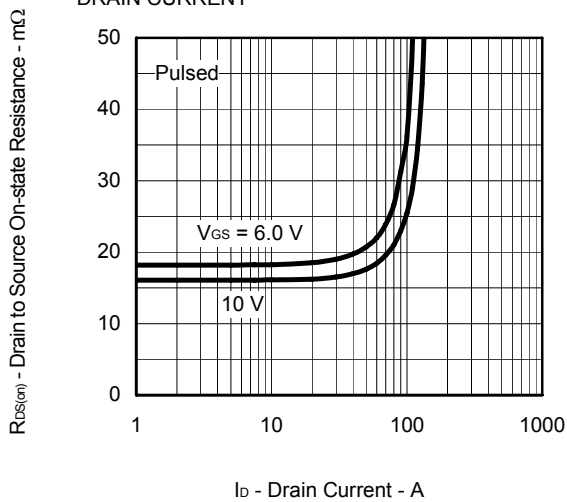
GATE TO SOURCE THRESHOLD VOLTAGE vs. CHANNEL TEMPERATURE



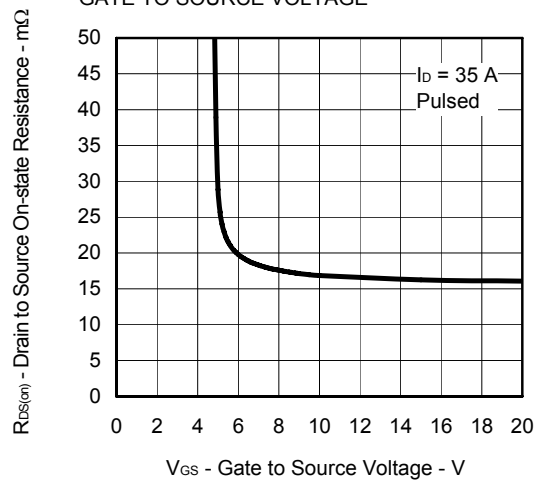
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



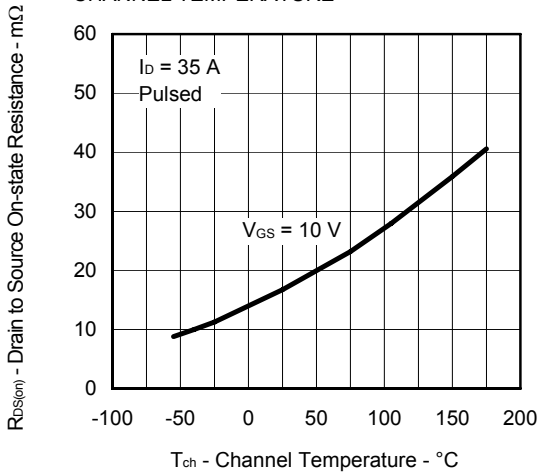
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



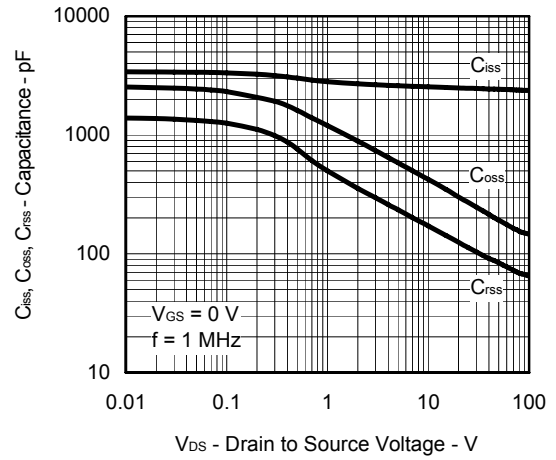
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



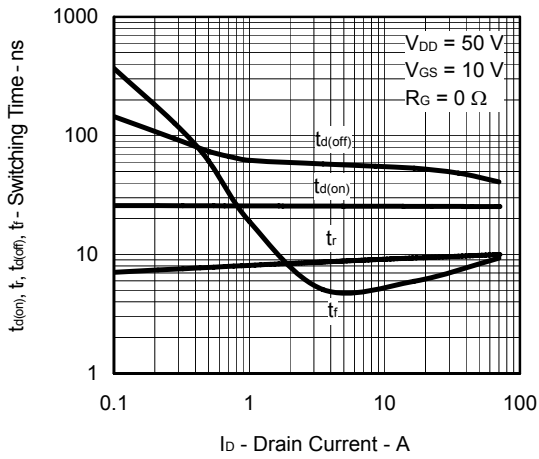
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



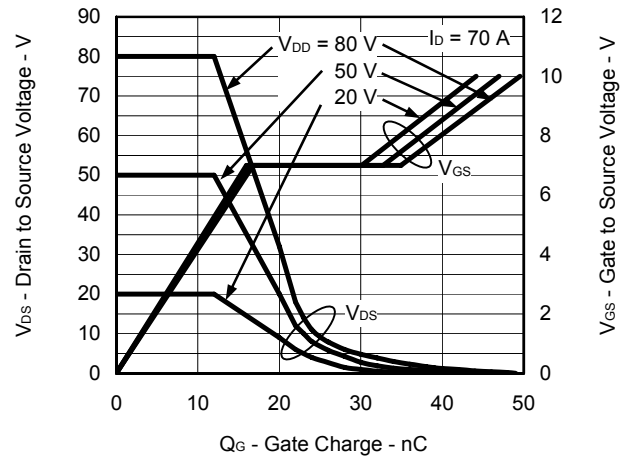
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



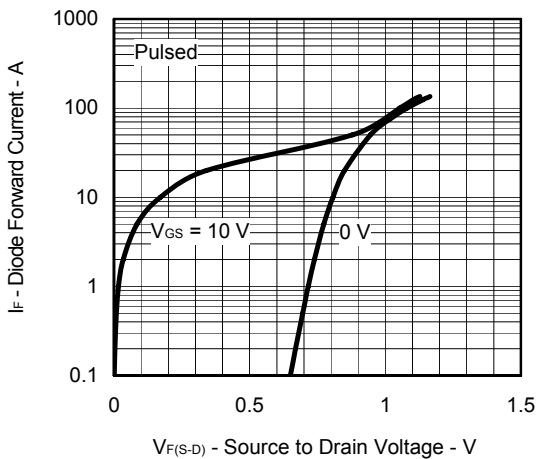
SWITCHING CHARACTERISTICS



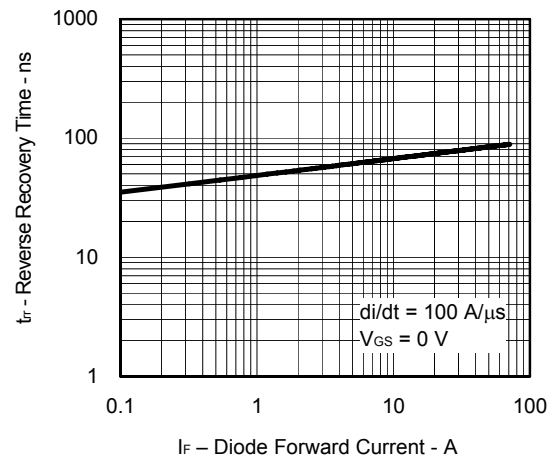
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



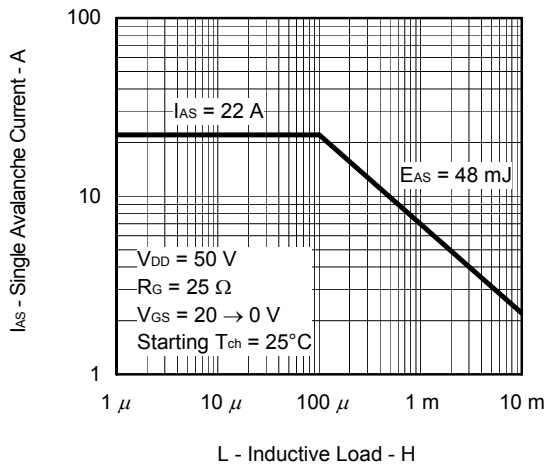
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



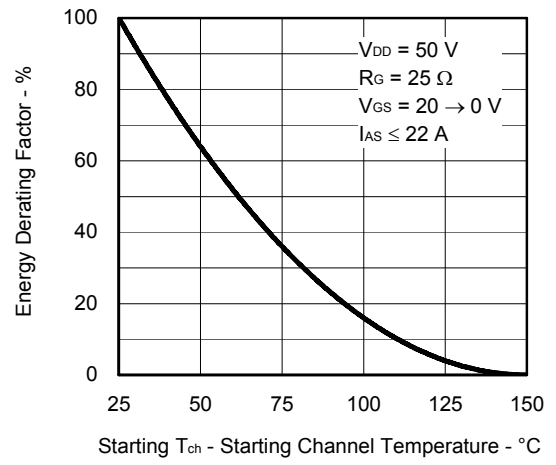
REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT



SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD

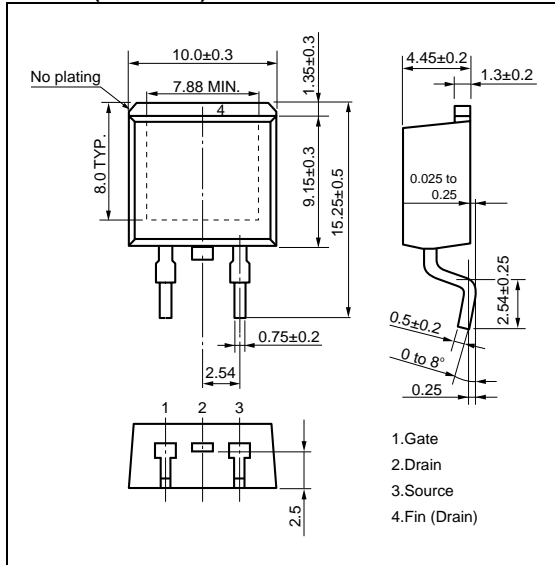


SINGLE AVALANCHE ENERGY DERATING FACTOR

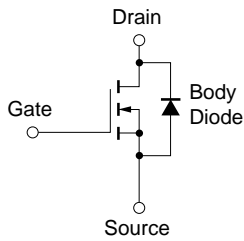


PACKAGE DRAWING (Unit: mm)

TO-263 (MP-25ZK)



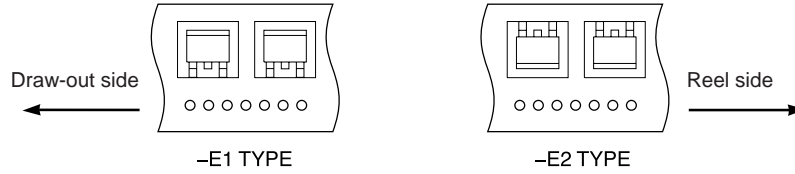
EQUIVALENT CIRCUIT



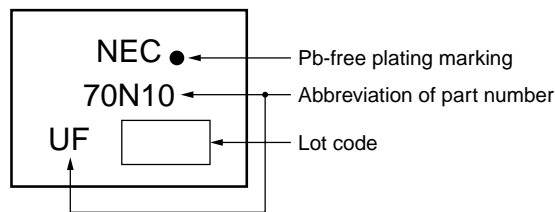
Remark Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

<R> **TAPE INFORMATION**

There are two types (-E1, -E2) of taping depending on the direction of the device.



MARKING INFORMATION



RECOMMENDED SOLDERING CONDITIONS

The NP70N10KUF should be soldered and mounted under the following recommended conditions.

For soldering methods and conditions other than those recommended below, please contact an NEC Electronics sales representative.

For technical information, see the following website.

Semiconductor Device Mount Manual (<http://www.necel.com/pkg/en/mount/index.html>)

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared reflow	Maximum temperature (Package's surface temperature): 260°C or below Time at maximum temperature: 10 seconds or less Time of temperature higher than 220°C: 60 seconds or less Preheating time at 160 to 180°C: 60 to 120 seconds Maximum number of reflow processes: 3 times Maximum chlorine content of rosin flux (percentage mass): 0.2% or less	IR60-00-3
Partial heating	Maximum temperature (Pin temperature): 350°C or below Time (per side of the device): 3 seconds or less Maximum chlorine content of rosin flux: 0.2% (wt.) or less	P350

Caution Do not use different soldering methods together (except for partial heating).

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